

2 A ultra low V_F MEGA Schottky barrier rectifier Rev. 04 — 30 December 2008 Pr

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in SOD323 (SC-76) very small Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Forward current: $I_F \le 2 A$
- Reverse voltage: V_R ≤ 10 V
- Ultra low forward voltage
- Very small SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current	$T_{sp} \le 55 \ ^{\circ}C$	-	-	2	А
V _R	reverse voltage		-	-	10	V
V _F	forward voltage	I _F = 1 A	<u>[1]</u> _	280	350	mV



2 A ultra low V_F MEGA Schottky barrier rectifier

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	e Graphic symbol
1	cathode	[1]	
2	anode	anode 1 2	1 1 2
			sym001

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Orde	ring informati	on	
Type number	Package		
	Name	Description	Version
PMEG1020EA	SC-76	plastic surface-mounted package; 2 leads	SOD323

4. Marking

Table 4. Marking o	odes
Type number	Marking code
PMEG1020EA	E2

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0,	,		
Symbol	Parameter	Conditions	Min	Max	Unit
V _R	reverse voltage		-	10	V
I _F	forward current	$T_{sp} \le 55 \ ^{\circ}C$	-	2	А
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ ms}; \delta \le 0.5$	-	3.2	А
I _{FSM}	non-repetitive peak forward current	square wave; t _p = 8 ms	-	9	А
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

2 A ultra low V_F MEGA Schottky barrier rectifier

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	450	K/W
			[2] _	-	210	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[3]</u> _	-	90	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB with copper clad 10×10 mm.

[3] Soldering point of cathode tab.

7. Characteristics

Table 7. Characteristics

$T_{amb} = 25 \circ C$ unless otherwise specified.

unio	1					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VF	forward voltage		<u>[1]</u>			
		I _F = 0.01 A	-	100	130	mV
		I _F = 0.1 A	-	170	200	mV
		I _F = 1 A	-	280	350	mV
		I _F = 2 A	-	350	460	mV
Ι _R	reverse current		[2]			
		V _R = 5 V	-	0.7	2	mA
		V _R = 8 V	-	1	2.5	mA
		V _R = 10 V	-	1.2	3	mA
C _d	diode capacitance	V _R = 5 V; f = 1 MHz	-	37	45	pF

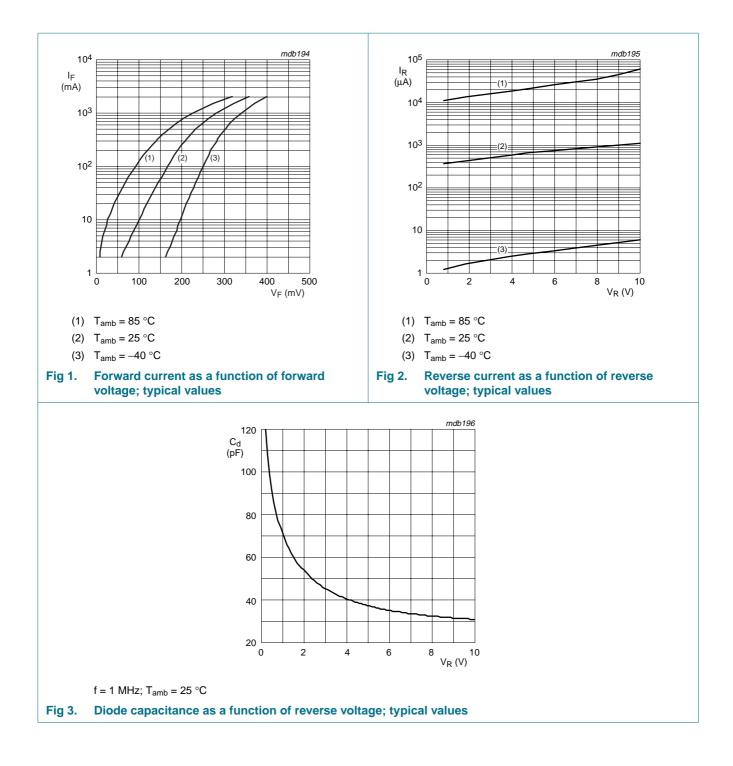
[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

[2] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

NXP Semiconductors

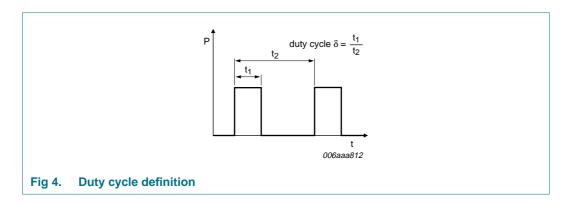
PMEG1020EA

2 A ultra low V_F MEGA Schottky barrier rectifier

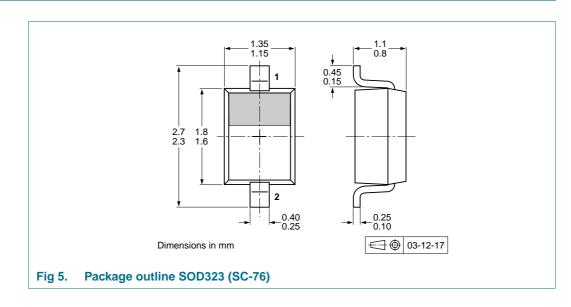


2 A ultra low V_F MEGA Schottky barrier rectifier

8. Test information



9. Package outline



10. Packing information

Table 8. Packing methods

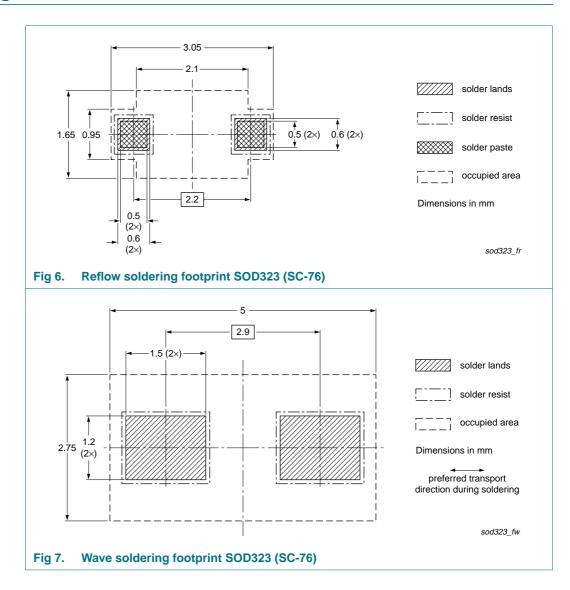
The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMEG1020EA	SOD323	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

2 A ultra low V_F MEGA Schottky barrier rectifier

11. Soldering



2 A ultra low V_F MEGA Schottky barrier rectifier

12. Revision history

Table 9. Revision histo	ory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG1020EA_4	20081230	Product data sheet	-	PMEG1020EA_3
Modifications:		f this data sheet has been red NXP Semiconductors.	esigned to comply w	ith the new identity
	 Legal texts h 	ave been adapted to the new o	company name wher	re appropriate.
	 Section 13 "L 	_egal information": updated		
PMEG1020EA_3	20040206	Product specification	-	PMEG1020EA_2
PMEG1020EA_2	20030715	Product specification	-	PMEG1020EA_1
PMEG1020EA_1	20030307	Preliminary specification	-	-

2 A ultra low V_F MEGA Schottky barrier rectifier

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

13.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

14. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

NXP Semiconductors

PMEG1020EA

2 A ultra low V_F MEGA Schottky barrier rectifier

15. Contents

1	Product profile	1
1.1	General description.	1
1.2	Features	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	3
7	Characteristics	3
8	Test information	5
9	Package outline	5
10	Packing information	5
11	Soldering	6
12	Revision history	7
13	Legal information	B
13.1	Data sheet status 8	8
13.2	Definitions	В
13.3	Disclaimers	8
13.4	Trademarks	В
14	Contact information	8
15	Contents	9

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2009.

All rights reserved.



Date of release: 30 December 2008 Document identifier: PMEG1020EA_4

